

/ Descriptions

WR0<5 M M E SQS æ M ç s ll 1 Silicon PNP transistor in a TO-92 Plastic Package.

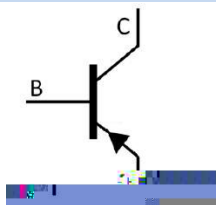
/ Features

æ ç ð ll ' ll ð ll ð ç ð ll æ "Q I ' ' High P_C and I_C .

/ Applications

æ ç æ A I ' æ ç Medium power amplifier applications.

/ Equivalent Circuit



/ Pinning



PIN1 χ Collector PIN 2 χ Base PIN 3 χ Emitter

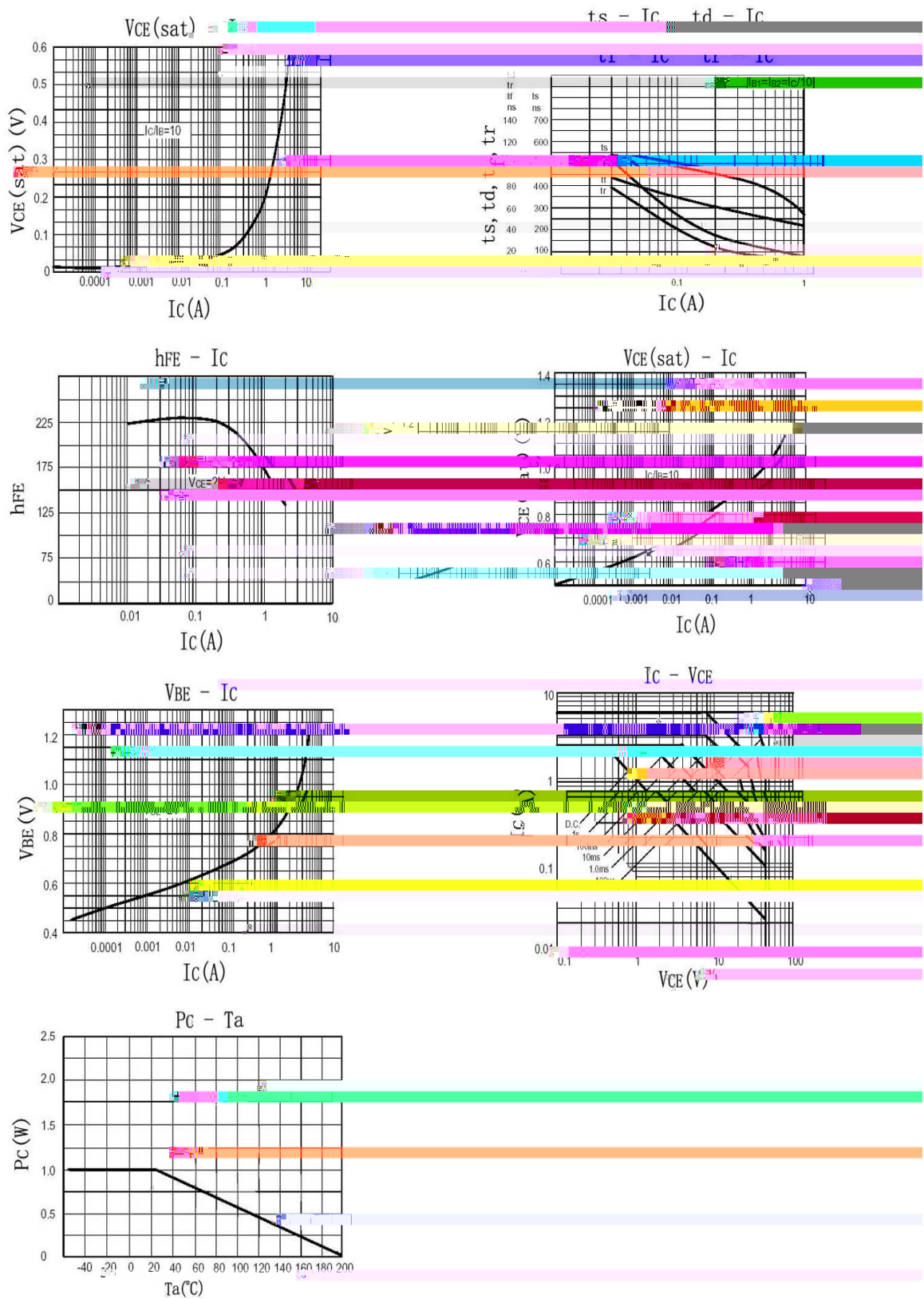
/ hFE Classifications & Marking

ø M ç ç " See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-60	V
Collector to Emitter Voltage	V_{CEO}	-45	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-2.0	A
Peak Collector Current- Continuous	I_{CM}	-6.0	A
Collector Power Dissipation	P_C	1.0	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C = -100\mu A$	-60			V
Collector to Emitter Breakdown Voltage	V	$I = -10mA$	-45			V

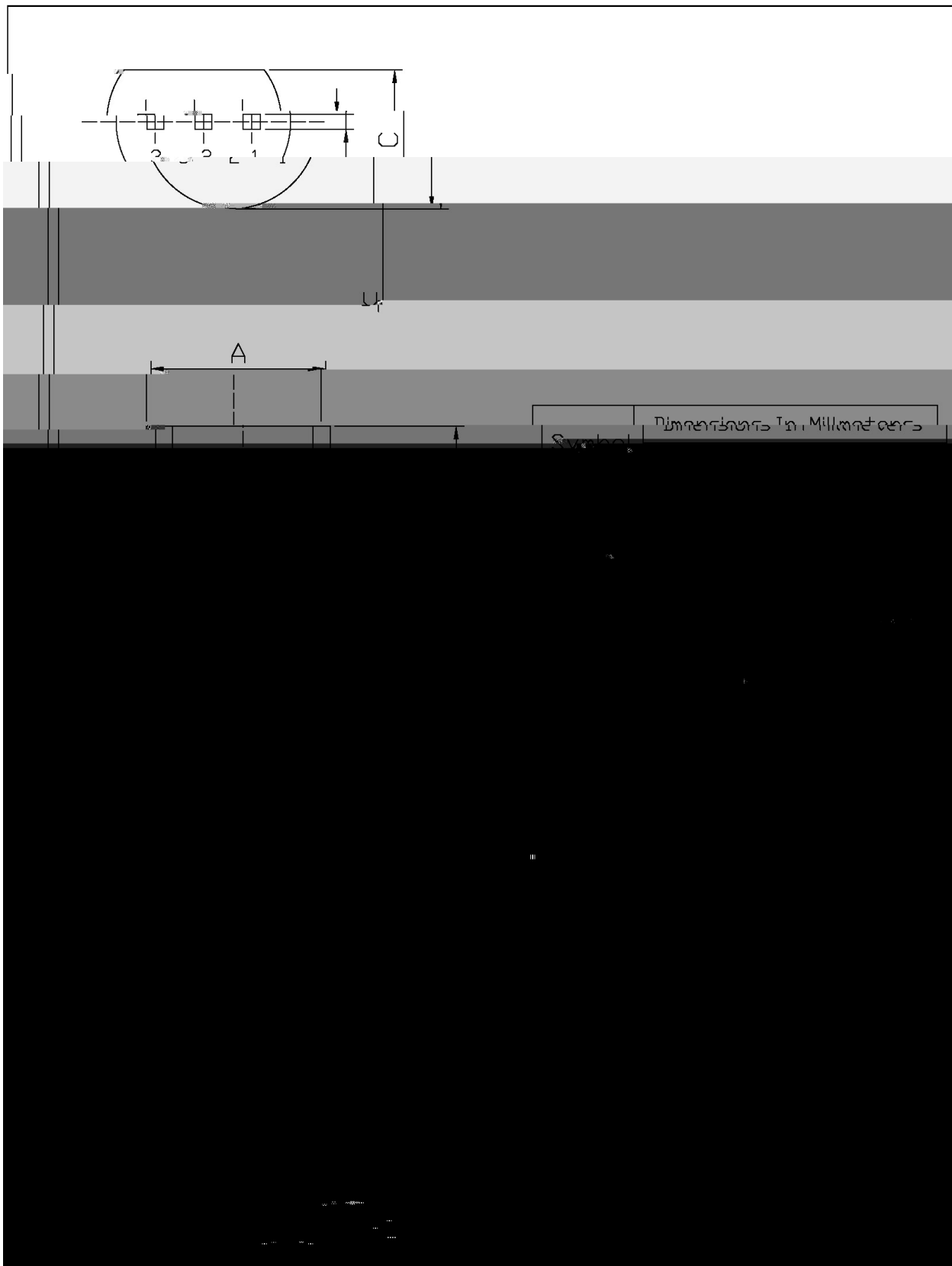
/ Electrical Characteristic Curve



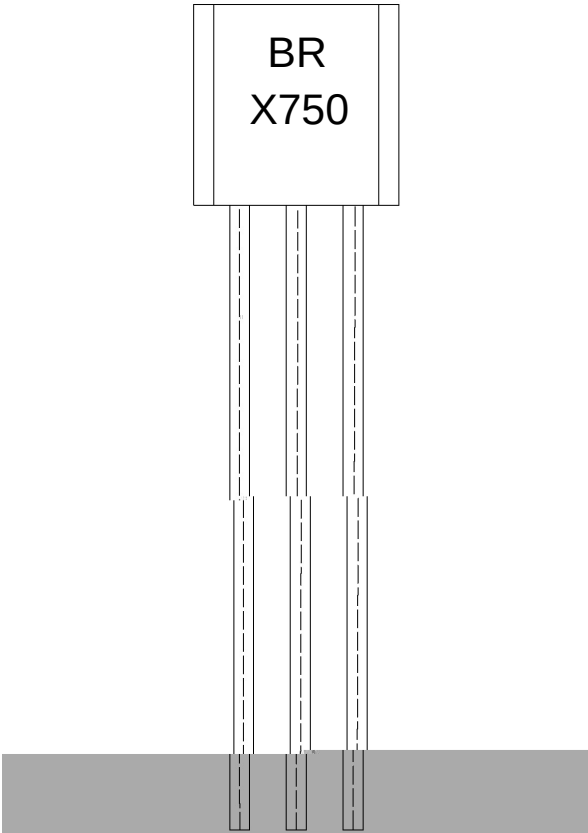
/ Package Dimensions

T0-92

Unit: mm



/ Marking Instructions



BR	公司代码
X750	产品型号
----	公司代码 产品型号 公司代码 产品型号
Note:	
BR:	Company Code.
X750:	Product Type.
****:	Lot No. Code,code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



说明

1. 预加热: 25~150 °C, Time: 60~90sec;
2. 峰值温度: 255 °C, Time: 5~0.5sec;
3. 冷却速度: 2~10 °C/sec.

Note:

- 1.Preheating:25~150 °C, Time:60~90sec.
- 2.Peak Temp.:255 °C, Duration:5~0.5sec.
3. Cooling Speed: 2~10 °C/sec.

/ Resistance to Soldering Heat Test Conditions

温度: 270 ± 5 °C 时间: 10 ± 1 sec. Temp: 270 ± 5 Time: 10 ± 1 sec

/ Packaging SPEC.

散装 / BULK

Package Type	Units					Dimension		(unit mm3)

Ammo

Package Type	Units	Dimension	(unit mm3)
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